ICMOVPE XXII
July 12 (Sun.) – 17 (Fri.), 2026
ICC JEJU, Jeju Island, Korea

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Andre Maaßdorf was born in Berlin, Germany, 1975. He received the diploma degree in Physics from Humboldt University of Berlin, Germany, in 2000 for his work on time-resolved photoluminescence on heavily doped GaAs. Since 1998 he is with the Ferdinand-Braun-Institute, Berlin, Germany, and obtained his Ph.D. in Physics at the Technical University of Berlin, Germany, in 2008 for his work on GaAs-based high-power Heterojunction Bipolar Transistors (HBTs).

As the head of the Arsenides&Phosphides epitaxy group within the Materials Technology Dept. at FBH his present work is focused on MOVPE for a variety of GaAs-based electro-optical devices, most prominently on the design and growth of vertical cavity surface emitting lasers (VCSELs), edge emitting laser diodes and the realization of highly efficient tunnel junctions. He has (co-)authored more than 120 publications on GaAs growth and GaAs-based devices.